

METHOD FOR TREATING PHOTOLITHOGRAPHIC DEVELOPER AND
STRIPPER WASTE STREAMS CONTAINING RESIST OR SOLDER MASK AND
GAMMA BUTYROLACTONE OR BENZYL ALCOHOL

ABSTRACT

A method is disclosed for using the simple, environmentally-friendly organic compounds gamma-butyrolactone and benzyl alcohol to develop and to strip free radical-initiated, addition polymerizable resists, cationically cured resists and solder masks and Vacrel photoresists. In all cases the developers and strippers include gamma butyrolactone or benzyl alcohol. The developers and strippers optionally also include a minor amount of methanol, ethanol, isopropyl alcohol, propylene glycol monomethylacetate, ethylene glycol monomethyl ether, formamide, nitromethane, propylene oxide, or methyl ethyl ketone, acetone and water. During development of the photopatterned resist or solder mask, the unpolymerized regions are dissolved in the disclosed developers.